IN THE CLAIMS:

Please amend claims 1-8 and add new claims 9-20 as provided below:

1. (Currently amended): A ~~P~~process for etching at least one substrate ~~(10)~~, ~~in particular~~comprising at least one silicon wafer for the fabrication of DRAM memory chips, ~~in which~~wherein

~~a)~~ at least one substrate ~~(10)~~, for a first etching step ~~(1)~~, is arranged for a predetermined time in a first vessel containing a first etchant, then

~~b)~~ at least one substrate ~~(10)~~, for a first rinsing step ~~(2)~~, is arranged for a predetermined time in a second vessel containing a first rinsing agent, the first rinsing agent containing at least one wetting agent, and then

~~c)~~ at least one substrate ~~(10)~~, for a second etching step ~~(3)~~, is arranged for a predetermined time in a third vessel containing a second etchant.

2. (Currently amended): The ~~P~~process according to Claim 1, ~~characterized in that~~ wherein for at least one substrate ~~(10)~~, after the second etching step ~~(3)~~, a second rinsing step is carried out using a second rinsing agent in a fourth vessel.

3. (Currently amended): The ~~P~~process according to Claim 2, ~~characterized in that~~ wherein for at least one substrate ~~(10)~~ a drying step ~~(5)~~ is carried out after the second rinsing step ~~(3)~~.

4. (Currently amended): The ~~P~~process according to Claim 1, ~~characterized in that~~ wherein the first etchant includes a hydrofluoric acid fraction.

5. (Currently amended): The ~~P~~process according to Claim 1, ~~characterized in that~~ wherein the second etchant includes an ammonia water (NH_4OH) fraction.

6. (Currently amended): The ~~P~~process according to Claim 5, ~~characterized in that~~ wherein the first rinsing agent contains the wetting agent in a concentration in the range from 0.01 to 0.1% by weight.

7. (Currently amended): The ~~P~~process according to Claim 1, ~~characterized in that~~ wherein in the second etching step ~~(3)~~ at least one structure ~~(11)~~ with an aspect ratio in the range from 10 to 50 is introduced into the substrate ~~(10)~~.

8. (Currently amended): The ~~P~~process according to Claim 7, ~~characterized in that~~ wherein the structure ~~(11)~~ ~~is~~comprises at least one deep trench structure for a DRAM memory cell.

9. (New): The process according to Claim 1, wherein in the second etching step at least one structure with an aspect ratio of greater than 50 is introduced into the substrate.

10. (New): A method of etching a substrate, comprising:

arranging the substrate in a first vessel containing a first etchant;

performing a first etching of the substrate using the first etchant in the first vessel;

arranging the substrate in a second vessel containing a first rinsing agent comprising at least one wetting agent;

performing a first rinsing of the substrate with the first rinsing agent in the second vessel for a first predetermined time period;

arranging the substrate in a third vessel containing a second etchant; and

performing a second etching of the substrate using the second etchant in the third vessel for a second predetermined period of time.

11. (New): The method of Claim 10, wherein the substrate comprises a silicon semiconductor substrate.

12. (New): The method of Claim 11, wherein the silicon substrate are employed in a fabrication of DRAM memory chips.

13. (New): The method of Claim 10, further comprising performing a second rinsing of the substrate using a second rinsing agent in a fourth vessel.

14. (New): The method of Claim 13, further comprising drying the substrate after the second rinsing.

15. (New): The method of Claim 10, wherein the first etchant comprises a hydrofluoric acid fraction.

16. (New): The method of Claim 10, wherein the second etchant comprises an ammonia water (NH_4OH) fraction.

17. (New): The method of Claim 10, wherein the first rinsing agent contains the wetting agent in a concentration in the range from about 0.01% to about 0.1% by weight.

18. (New): The process according to Claim 10, wherein the second etching results in at least one structure formed within the substrate comprising an aspect ratio in the range of about 10 to about 50, wherein the at least one structure comprises at least one deep trench structure associated with a DRAM memory cell.

19. (New): The process according to Claim 10, wherein the second etching results in at least one structure formed within the substrate comprising an aspect ratio of greater than about 50.

20. (New): The process according to Claim 10, wherein the second etching results in at least one structure formed within the substrate comprising an aspect ratio in the range of about 10 to about 80.